

INFRARED DIODE LASER AT 808nm

RN-I-808/1~2500mW

产品描述

Diode infrared laser module at 808nm is made features of ultra compact, long

lifetime, low cost and easy operating, which is used in measurement, communication,

spectrum analysis, etc.

产品参数

RN-I-808/1~2500mW	
Wavelength (nm)	808±3
Operating mode	CW
Output power (mW)	>1, 100, 200, 300,, 2500
Power stability (rms, over 4 hours)	<1%, <3%, <5%
Transverse mode	Multimode
Dimensions of beam at the aperture (mm)	~5×8
Beam divergence, full angle (mrad)	<3.0
Warm-up time (minutes)	<5
Beam height from base plate (mm)	24. 8
Operating temperature (℃)	10~35
Power supply	PSU-III-OEM
TTL / Analog modulation	TTL or Analog with 1Hz-1KHz 1KHz-10KHz, 10KHz-30KHz optional
Expected lifetime (hours)	10000
Warranty	1 year

北京市昌平区 国家信息产业基地立业路13号2011 ≤ sales@ranbond.com

010-57513647